

# MMDT5451

Rev.B Jul.-2022

## 描述 / Descriptions

SOT-363 塑封封装 NPN+PNP 半导体三极管。

Silicon NPN and PNP transistor in a SOT-363 Plastic Package.

## 特征 / Features

高  $h_{FE}$  , 低  $V_{CE(sat)}$  , 无卤产品。

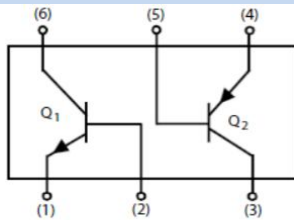
High DC Current Gain, Low Collector to Emitter Saturation Voltage, HF Product.

## 用途 / Applications

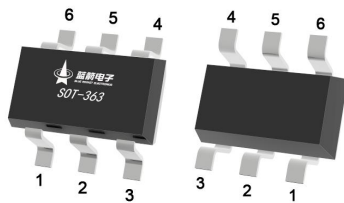
用于普通放大及开关。

General purpose amplifier and switching.

## 内部等效电路 / Equivalent Circuit



## 引脚排列 / Pinning



PIN 1、4 : Emitter

PIN 2、5 : Base

PIN 3、6 : Collector

## 放大及印章代码 / $h_{FE}$ Classifications & Marking

See Marking Instructions.

**极限参数 / Absolute Maximum Ratings(Ta=25°C) (Q1:NPN)**

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Collector to Base Voltage	$V_{CBO}$	180	V
Collector to Emitter Voltage	$V_{CEO}$	160	V
Emitter to Base Voltage	$V_{EBO}$	6.0	V
Collector Current	$I_C$	200	mA
Power Dissipation	$P_D$	200	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	625	°C/W
Junction and Storage Temperature	$T_j, T_{stg}$	-55~+150	°C

**极限参数 / Absolute Maximum Ratings(Ta=25°C) (Q2:PNP)**

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Collector to Base Voltage	$V_{CBO}$	-180	V
Collector to Emitter Voltage	$V_{CEO}$	-160	V
Emitter to Base Voltage	$V_{EBO}$	-6.0	V
Collector Current	$I_C$	-200	mA
Power Dissipation	$P_D$	200	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	625	°C/W
Junction and Storage Temperature	$T_j, T_{stg}$	-55~+150	°C

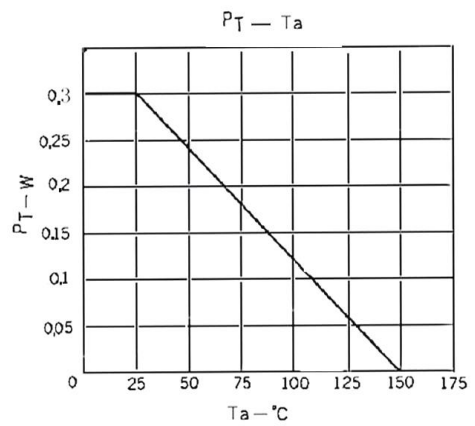
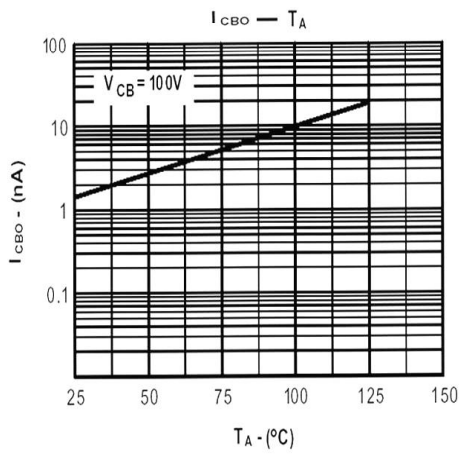
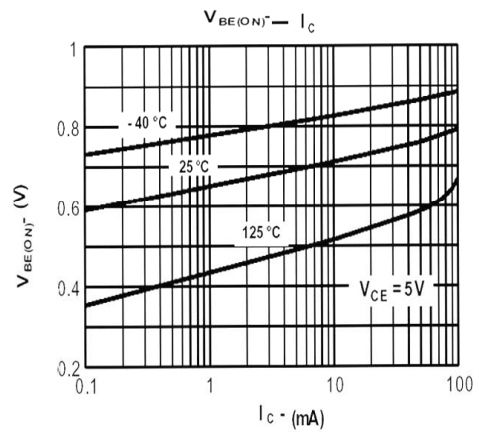
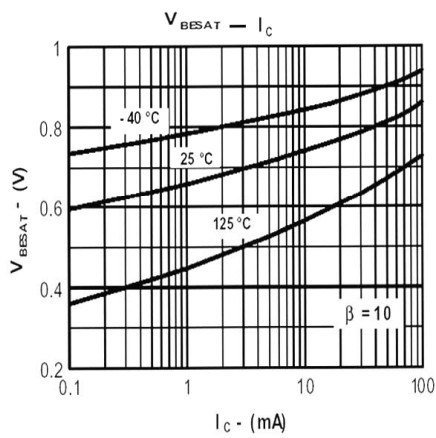
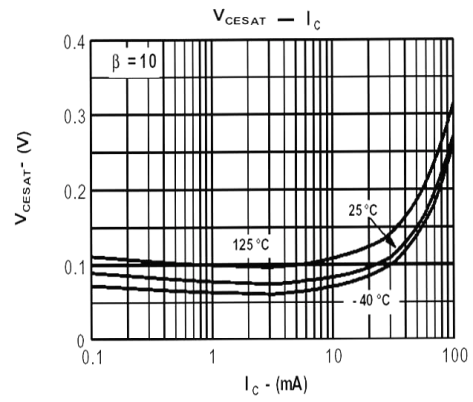
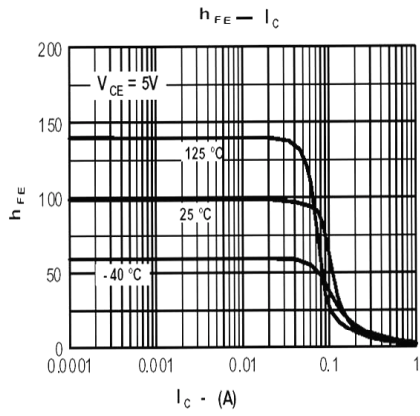
## 电性能参数 / Electrical Characteristics(Ta=25°C) (Q1:NPN)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Collector Cut-Off Current	$I_{CBO}$	$V_{CB}=180V$ $I_E=0$			0.1	$\mu A$
Emitter Cut-off Current	$I_{EBO}$	$V_{EB}=6.0V$ $I_C=0$			0.1	$\mu A$
DC Current Gain	$h_{FE(1)}$	$V_{CE}=5.0V$ $I_C=10mA$	50	200	400	
	$h_{FE(2)}$	$V_{CE}=5.0V$ $I_C=50mA$	20	160		
	$h_{FE(3)}$	$V_{CE}=5.0V$ $I_C=1.0mA$	40	190		
Collector-Emitter Saturation Voltage	$V_{CE(sat)(1)}$	$I_C=10mA$ $I_B=1.0mA$		0.06	0.15	V
	$V_{CE(sat)(2)}$	$I_C=50mA$ $I_B=5.0mA$		0.09	0.3	V
Base-Emitter Saturation Voltage	$V_{BE(sat)(1)}$	$I_C=10mA$ $I_B=1.0mA$		0.7	1.0	V
	$V_{BE(sat)(2)}$	$I_C=50mA$ $I_B=5.0mA$		0.8	1.0	V
Base-Emitter Voltage	$V_{BE}$	$V_{CE}=5.0V$ $I_C=10mA$		0.68	0.75	V
Transition Frequency	$f_T$	$V_{CE}=10V$ $I_C=10mA$	50	110		MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB}=10V$ $I_E=0$ $f=1.0MHz$		2.2	5.0	pF
Turn-on Time	$t_{on}$	$I_C=100mA$ $I_{B1}=-I_{B2}=10mA$		0.3		$\mu s$
Turn-off Time	$t_{off}$			0.4		$\mu s$
Storage Time	$t_{stg}$			0.2		$\mu s$

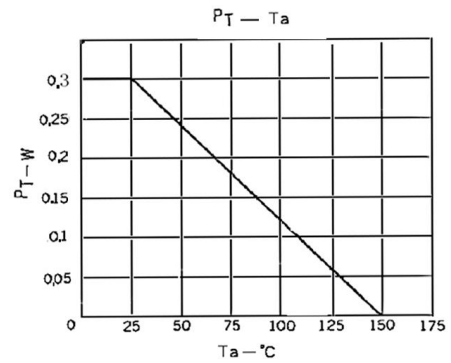
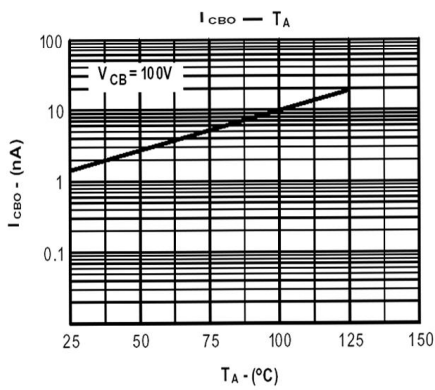
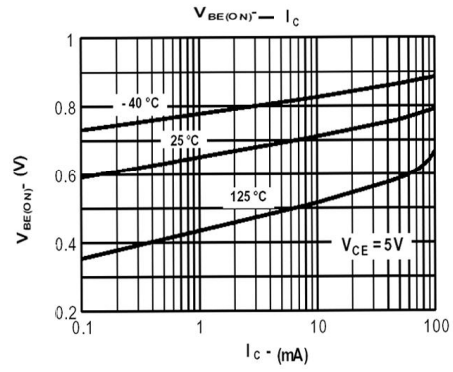
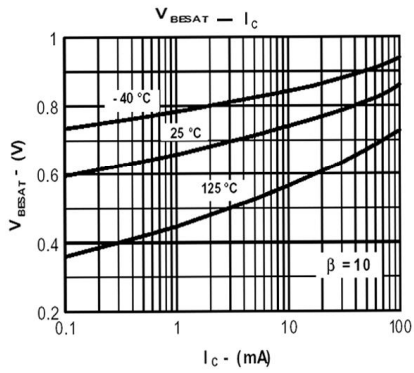
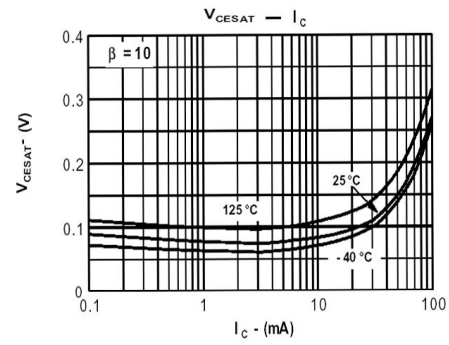
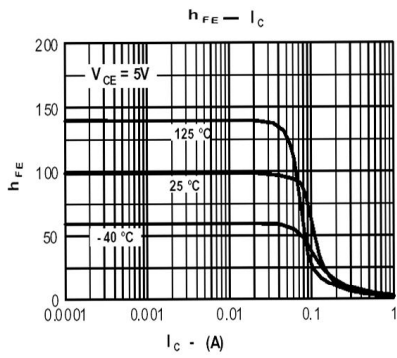
## 电性能参数 / Electrical Characteristics(Ta=25°C) (Q2:PNP)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Collector Cut-Off Current	$I_{CBO}$	$V_{CB}=-180V$ $I_E=0$			-0.1	$\mu A$
Emitter Cut-Off Current	$I_{EBO}$	$V_{EB}=-6.0V$ $I_C=0$			-0.1	$\mu A$
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-5.0V$ $I_C=-10mA$	50	200	400	
	$h_{FE(2)}$	$V_{CE}=-5.0V$ $I_C=-50mA$	20	70		
	$h_{FE(3)}$	$V_{CE}=-5.0V$ $I_C=-1.0mA$	40	180		
Collector-Emitter Saturation Voltage	$V_{CE(sat)(1)}$	$I_C=-10mA$ $I_B=-1.0mA$		-0.12	-0.4	V
	$V_{CE(sat)(2)}$	$I_C=-50mA$ $I_B=-5.0mA$		-0.5	-0.8	V
Base-Emitter Saturation Voltage	$V_{BE(sat)(1)}$	$I_C=-10mA$ $I_B=-1.0mA$		-0.75	-1.0	V
	$V_{BE(sat)(2)}$	$I_C=-50mA$ $I_B=-5.0mA$		-0.8	-1.0	V
Base-Emitter Voltage	$V_{BE}$	$V_{CE}=-5.0V$ $I_C=-10mA$		-0.7	-0.75	V
Transition Frequency	$f_T$	$V_{CE}=-10V$ $I_C=-10mA$	50	80		MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB}=-10V$ $I_E=0$ $f=10MHz$		2.5	5.0	pF
Turn-on Time	$t_{on}$	$I_C=-100mA$ $-I_{B1}=I_{B2}=-10mA$		0.1		$\mu s$
Storage Time	$t_{off}$			0.2		$\mu s$
Fall Time	$t_{stg}$			0.1		$\mu s$

电参数曲线图 / Electrical Characteristic Curve (Q1:NPN)

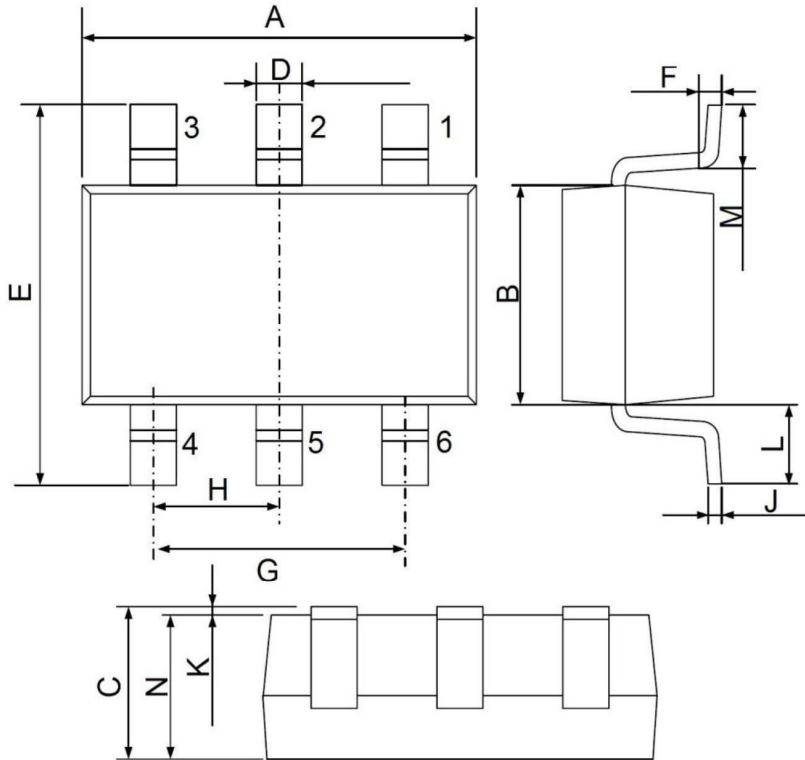


电参数曲线图 / Electrical Characteristic Curve (Q2:PNP)



外形尺寸图 / Package Dimensions

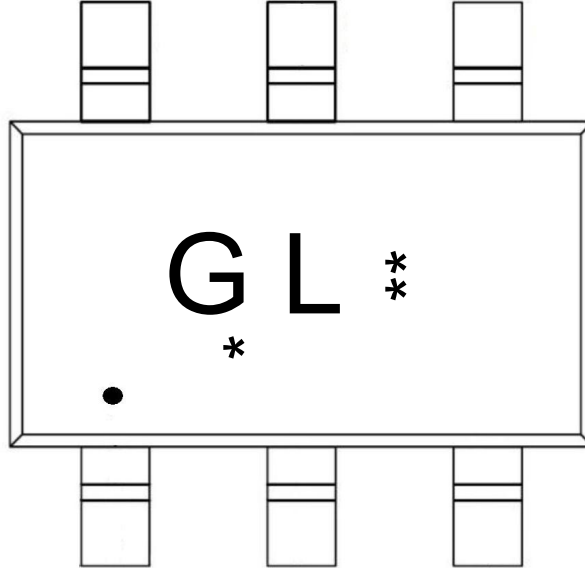
### SOT-363-6L



UNIT: mm

DIM	MIN	MAX
A	2.00	2.20
B	1.15	1.35
C	0.90	1.10
D	0.15	0.35
E	1.95	2.25
F	0.20 Typ.	
G	1.20	1.40
H	0.65 Typ.	
J	0.08	0.15
K	0.00	0.10
L	0.525 Ref.	
M	0.26	0.46
N	0.90	1.10

印章说明 / Marking Instructions



说明：

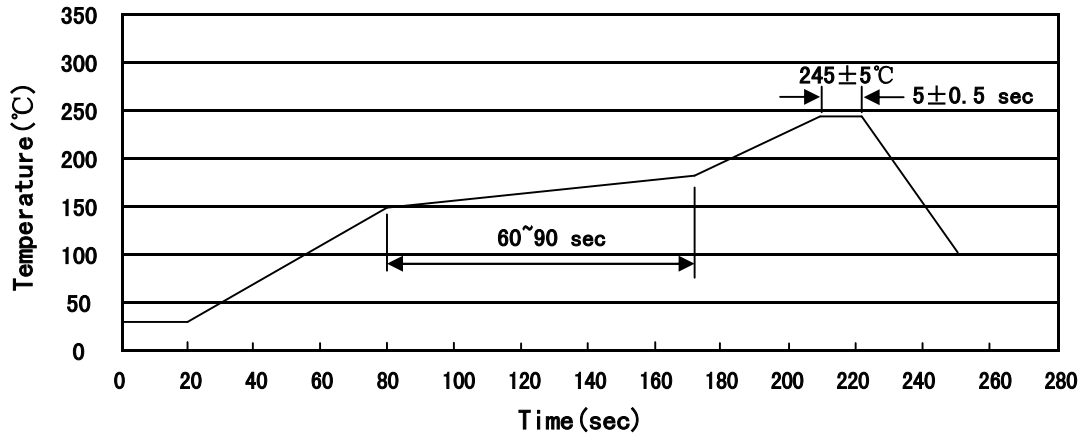
- ： 为“1”脚
- GL： 为型号代码
- \*\*\*： 为生产批号代码，随生产批号变化

Note:

- ： "1" Pin
- GL： Product Type Code
- \*\*\*: Lot No. Code, code change with Lot No



**回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)**



说明：

- 1、预热温度 150~180°C，时间 60~90sec;
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2~10°C/sec.

Note:

- 1.Preheating:150~180°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

**耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions**

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

**包装规格 / Packaging SPEC.**

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm <sup>3</sup> )		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT-363	3,000	10	30,000	6	180,000	7" ×8	180×120×180	390×385×205

**使用说明 / Notices**